

BAR28

SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching.

Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range.

Matched batches are available on request.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	75	V
l _F	Forward Continuous Current* $T_a = 25$ C	15	mA
I _{FSM}	Surge non Repetitive Forward Current* $\mu_p \le 1$ s	50	mA
T _{stg} Tj	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	°C
TL	Maximum Lead Temperaturc for Soldering during its at 4mm from Case	230	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-a)}	Junction-ambient*	400	°C/W

ELECTPICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
V _{BR}	$\tau_{amp} = 25^{\circ}CI_{R} = 10\mu A$	70			V
V _F * *	$T_{amb} = 25^{\circ}CI_F = 1mA$			0.41	V
S	$T_{amb} = 25^{\circ}CI_F = 15mA$			1	
I _R * *	$T_{amb} = 25^{\circ}CV_{R} = 50V$			0.2	μA

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
С	$T_{amb} = 25^{\circ}CV_{R} = 0Vf = 1MHz$			2	рF
τ	T _{amb} = 25°CI _F = 5mA Krakauer Method			100	ps

* On infinite heatsink with 4mm lead length
** Pulse test: tp

 ③ 300μs δ < 2%.

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

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Fig. 1: Forward current versus forward voltage at low level (typical values).

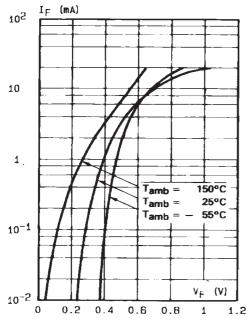


Fig. 2: Capacitance C versus reverse applied voltage V_R (typical values).

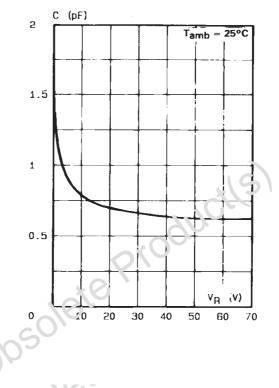


Fig. 3: Reverse current versus ambie. It lemperature.

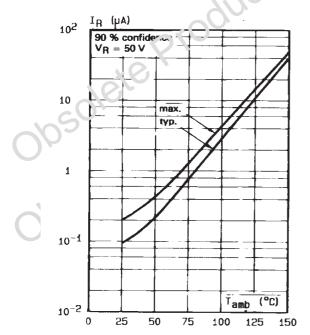
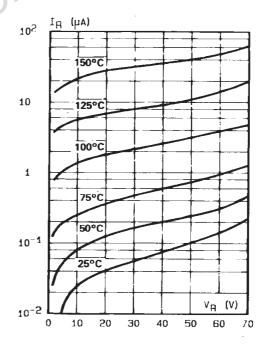


Fig. 4: Reverse current versus continuous reverse voltage (typical values).

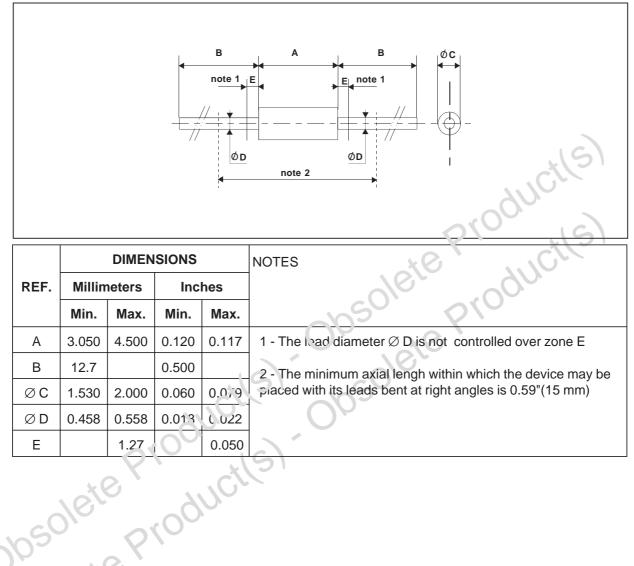


57

Cooling method : by convection and conduction Marking: clear, ring at cathode end.

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PACKAGE MECHANICAL DATA



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